Automotive Inductive Load Driver

This micro-integrated part provides a single component solution to switch inductive loads such as relays, solenoids, and small DC motors without the need of a free-wheeling diode. It accepts logic level inputs, thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides Robust Interface between D.C. Relay Coils and Sensitive Logic
- Capable of Driving Relay Coils Rated up to 150 mA at 12 Volts
- Replaces 3 or 4 Discrete Components for Lower Cost
- Internal Zener Eliminates Need for Free-Wheeling Diode
- Meets Load Dump and other Automotive Specs
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These are Pb–Free Devices

Typical Applications

- Automotive and Industrial Environment
- Drives Window, Latch, Door, and Antenna Relays

Benefits

- Reduced PCB Space
- Standardized Driver for Wide Range of Relays
- Simplifies Circuit Design and PCB Layout
- Compliance with Automotive Specifications



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS





ORDERING INFORMATION

Device	Package	Shipping [†]
NUD3124LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SZNUD3124LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
NUD3124DMT1G	SC–74 (Pb–Free)	3000 / Tape & Reel
SZNUD3124DMT1G	SC-74 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.



Symbol	Rating	Value	Unit
V _{DSS}	Drain-to-Source Voltage – Continuous (T _J = 125°C)	28	V
V _{GSS}	Gate-to-Source Voltage – Continuous (T _J = 125°C)	12	V
Ι _D	Drain Current – Continuous (T _J = 125°C)	150	mA
Ez	Single Pulse Drain-to-Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T _J Initial = 85°C)	250	mJ
P _{PK}	Peak Power Dissipation, Drain-to-Source (Notes 1 and 2) (T _J Initial = 85°C)	20	W
E _{LD1}	Load Dump Suppressed Pulse, Drain-to-Source (Notes 3 and 4) (Suppressed Waveform: $V_s = 45 V$, $R_{SOURCE} = 0.5 \Omega$, T = 200 ms) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T _J Initial = 85°C)	80	V
E _{LD2}	Inductive Switching Transient 1, Drain-to-Source (Waveform: $R_{SOURCE} = 10 \Omega$, T = 2.0 ms) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T _J Initial = 85°C)	100	V
E _{LD3}	Inductive Switching Transient 2, Drain-to-Source (Waveform: $R_{SOURCE} = 4.0 \Omega$, T = 50 µs) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T _J Initial = 85°C)	300	V
Rev-Bat	Reverse Battery, 10 Minutes (Drain-to-Source) (For Relay's Coils/Inductive Loads of 80 Ω or more)	-14	V
Dual-Volt	Dual Voltage Jump Start, 10 Minutes (Drain-to-Source)	28	V
ESD	Human Body Model (HBM) According to EIA/JESD22/A114 Specification	2,000	V

MAXIMUM RATINGS (T_J = 25° C unless otherwise specified)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Nonrepetitive current square pulse 1.0 ms duration.
2. For different square pulse durations, see Figure 2.
3. Nonrepetitive load dump suppressed pulse per Figure 3.
4. For relay's coils/inductive loads higher than 80 Ω, see Figure 4.

THERMAL CHARACTERISTICS

Symbol	Rating	Value	Unit
T _A	Operating Ambient Temperature	-40 to 125	°C
Т _Ј	Maximum Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-65 to 150	°C
PD	Total Power Dissipation (Note 5)SOT-23Derating above 25°CSOT-23	225 1.8	mW mW/°C
PD	Total Power Dissipation (Note 5) SC-74 Derating above 25°C SC-74	380 3.0	mW mW/°C
R _{θJA}	Thermal Resistance Junction-to-Ambient (Note 5) SOT-23 SC-74 SC	556 329	°C/W

5. Mounted onto minimum pad board.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Drain to Source Sustaining Voltage (I _D = 10 mA)	V _{BRDSS}	28	34	38	V
$ \begin{array}{l} \mbox{Drain to Source Leakage Current} \\ (V_{DS} = 12 \ V, \ V_{GS} = 0 \ V) \\ (V_{DS} = 12 \ V, \ V_{GS} = 0 \ V, \ T_J = 125^{\circ}C) \\ (V_{DS} = 28 \ V, \ V_{GS} = 0 \ V) \\ (V_{DS} = 28 \ V, \ V_{GS} = 0 \ V, \ T_J = 125^{\circ}C) \\ \end{array} $	I _{DSS}			0.5 1.0 50 80	μΑ
$ \begin{array}{l} \mbox{Gate Body Leakage Current} \\ (V_{GS} = 3.0 \ V, \ V_{DS} = 0 \ V) \\ (V_{GS} = 3.0 \ V, \ V_{DS} = 0 \ V, \ T_J = 125^{\circ}C) \\ (V_{GS} = 5.0 \ V, \ V_{DS} = 0 \ V) \\ (V_{GS} = 5.0 \ V, \ V_{DS} = 0 \ V, \ T_J = 125^{\circ}C) \end{array} $	I _{GSS}		- - - -	60 80 90 110	μΑ
ON CHARACTERISTICS	<u></u>				-
Gate Threshold Voltage ($V_{GS} = V_{DS}$, $I_D = 1.0$ mA) ($V_{GS} = V_{DS}$, $I_D = 1.0$ mA, $T_J = 125^{\circ}$ C)	V _{GS(th)}	1.3 1.3	1.8 -	2.0 2.0	V
	R _{DS(on)}	- - -		1.4 1.7 0.8 1.1	Ω
Output Continuous Current ($V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}$) ($V_{DS} = 0.25 \text{ V}, V_{GS} = 3.0 \text{ V}, T_J = 125^{\circ}\text{C}$)	I _{DS} (on)	150 140	200	_	mA
Forward Transconductance $(V_{DS} = 12 \text{ V}, I_D = 150 \text{ mA})$	9FS	-	500	-	mmho
DYNAMIC CHARACTERISTICS	•				
Input Capacitance (V _{DS} = 12 V, V _{GS} = 0 V, f = 10 kHz)	Ciss	-	32	-	pf
Output Capacitance (V _{DS} = 12 V, V _{GS} = 0 V, f = 10 kHz)	Coss	-	21	_	pf
Transfer Capacitance $(V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 10 \text{ kHz})$	Crss	_	8.0	_	pf
SWITCHING CHARACTERISTICS	-	_	_	_	_
Propagation Delay Times: High to Low Propagation Delay; Figure 1, $(V_{DS} = 12 \text{ V}, V_{GS} = 3.0 \text{ V})$ Low to High Propagation Delay; Figure 1, $(V_{DS} = 12 \text{ V}, V_{GS} = 3.0 \text{ V})$	t _{PHL} t _{PLH}	-	890 912	_	ns
High to Low Propagation Delay; Figure 1, $(V_{DS} = 12 \text{ V}, V_{GS} = 5.0 \text{ V})$ Low to High Propagation Delay; Figure 1, $(V_{DS} = 12 \text{ V}, V_{GS} = 5.0 \text{ V})$	t _{PHL} t _{PLH}	-	324 1280	-	
Transition Times: Fall Time; Figure 1, (V _{DS} = 12 V, V _{GS} = 3.0 V) Rise Time; Figure 1, (V _{DS} = 12 V, V _{GS} = 3.0 V)	t _f t _r	-	2086 708	_	ns
Fall Time; Figure 1, (V _{DS} = 12 V, V _{GS} = 5.0 V) Rise Time; Figure 1, (V _{DS} = 12 V, V _{GS} = 5.0 V)	t _f t _r	- -	556 725	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CURVES

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$



Figure 1. Switching Waveforms





Figure 3. Load Dump Waveform Definition





Figure 13. Transient Thermal Response for NUD3124LT1G

APPLICATIONS INFORMATION



Figure 14. Applications Diagram





© Semiconductor Components Industries, LLC, 2019

onsemi

SC-74 CASE 318F ISSUE P

DATE 07 OCT 2021



special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Gate Drivers category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

 89076GBEST
 00053P0231
 56956
 57.404.7355.5
 LT4936
 57.904.0755.0
 5882900001
 00600P0005
 00-9050-LRPP
 00-9090-RDPP

 5951900000
 01-1003W-10/32-15
 0131700000
 00-2240
 LTP70N06
 LVP640
 5J0-1000LG-SIL
 LY1D-2-5S-AC120
 LY2-US-AC240
 LY3

 UA-DC24
 00576P0020
 00600P0010
 LZN4-UA-DC12
 LZNQ2M-US-DC5
 LZNQ2-US-DC12
 LZP40N10
 00-8196-RDPP
 00-8274-RDPP

 00-8275-RDNP
 00-8722-RDPP
 00-8728-WHPP
 00-8869-RDPP
 00-9051-RDPP
 00-9091-LRPP
 00-9291-RDPP
 0207100000
 0207400000

 01312
 0134220000
 60713816
 M15730061
 61161-90
 61278-0020
 6131-204-23149P
 6131-205-17149P
 6131-209-15149P
 6131-218-17149P

 6131-220-21149P
 6131-260-2358P
 6131-265-11149P
 6131-205-17149P
 6131-209-15149P
 6131-218-17149P